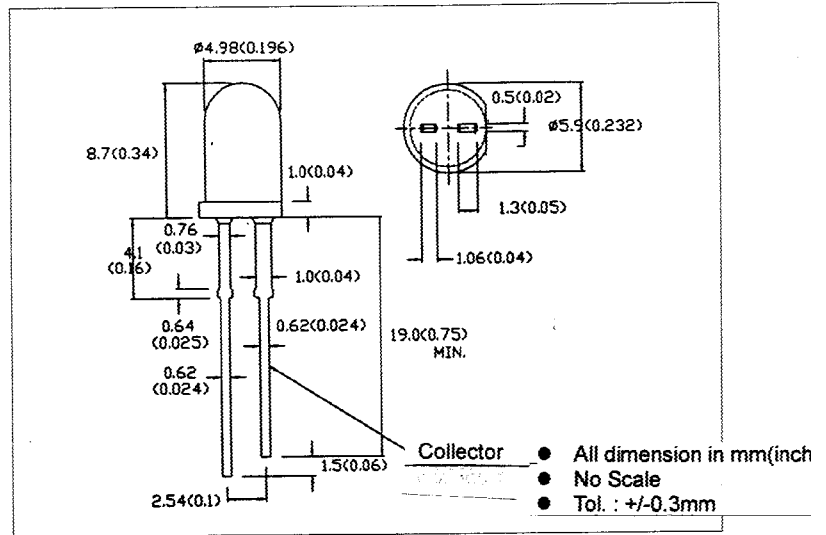


DESCRIPTION

MEL79 is NPN silicon planar photo-transistor with 5mm clear transparent lens. It features ultra high illumination sensitivity and fast response time.



ABSOLUTE MAXIMUM RATINGS

Collector-Emitter Voltage	V _{CEO}	30V
Emitter-Collector Voltage	V _{ECO}	5V
Continuous Power Dissipation	P _d	50mW
Operating Junction Temperature	T _j	-40 to +85°C
Storage Temperature Range	T _{stg}	-40 to +100°C
Lead Soldering Temperature (5 second, 1/16 inch from body)		260°C

ELECTRO-OPTICAL CHARACTERISTICS (T_a=25°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT	CONDITIONS
Collector-Emitter Breakdown Voltage	BV _{CEO}	30		V	I _C =100μA E _e =0
Emitter-Collector Breakdown Voltage	BV _{ECO}	5		V	I _C =100μA E _e =0
Dark Current	I _D		200	nA	V _{CE} =10V E _e =0
Light Current	I _L *	6.0		mA	V _{CE} =5V E _e =5mW/cm ²
Collector-Emitter Saturation Voltage	V _{CE(sat)}		0.3	V	I _C =500μA E _e =20mW/cm ²
Rise Time	T _r	15	TYP	μs	V _{CE} =5V I _C =1mA R _L =1Kohm
Fall Time	T _f	15	TYP	μs	V _{CE} =5V I _C =1mA R _L =1Kohm

* : Measured at noted irradiance as emitted from a tungsten filament lamp at a color temperature of 2354°K.



MICRO ELECTRONICS LTD.

38, Hung To Road, Microtron Building, Kwun Tong, Kowloon, Hong Kong.

Kwun Tong P.O. Box 69477 Hong Kong. Fax No. 2341 0321 Telex:43510 Micro Hx. Tel: 2343 0181-5